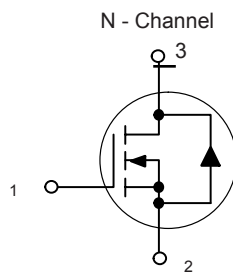


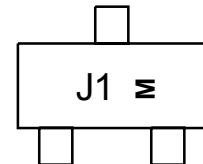
### N-Channel SOT-23

Typical applications are dc-dc converters, power management in portable and battery-powered products such as computers, printers, PCMCIA cards, cellular and cordless telephones.

- Low Threshold Voltage ( $V_{GS(th)}$ : 0.5V...1.5V) makes it ideal for low voltage applications
- Miniature SOT-23 Surface Mount Package saves board space
- **Pb-Free package is available**  
 RoHS product for packing code suffix "G"  
 Halogen free product for packing code suffix "H"



#### MARKING DIAGRAM & PIN ASSIGNMENT



J1 = Device Code  
 M = Month Code

#### MAXIMUM RATINGS ( $T_A = 25^\circ\text{C}$ unless otherwise noted)

Rating	Symbol	Value	Unit
Drain-to-Source Voltage	$V_{DSS}$	50	Vdc
Gate-to-Source Voltage – Continuous	$V_{GS}$	$\pm 20$	Vdc
Drain Current			mA
– Continuous @ $T_A = 25^\circ\text{C}$	$I_D$	200	
– Pulsed Drain Current ( $t_p \leq 10 \mu\text{s}$ )	$I_{DM}$	800	
Total Power Dissipation @ $T_A = 25^\circ\text{C}$	$P_D$	225	mW
Operating and Storage Temperature Range	$T_J, T_{stg}$	-55 to 150	$^\circ\text{C}$
Thermal Resistance – Junction-to-Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Maximum Lead Temperature for Soldering Purposes, for 10 seconds	$T_L$	260	$^\circ\text{C}$

#### ORDERING INFORMATION

Device	Package	Shipping
BSS138LT1	SOT-23	3000 Tape & Reel

**ELECTRICAL CHARACTERISTICS** ( $T_A = 25^\circ\text{C}$  unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
<b>OFF CHARACTERISTICS</b>					
Drain-to-Source Breakdown Voltage ( $V_{GS} = 0\text{ Vdc}$ , $I_D = 250\ \mu\text{Adc}$ )	$V_{(BR)DSS}$	50	–	–	Vdc
Zero Gate Voltage Drain Current ( $V_{DS} = 25\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ ) ( $V_{DS} = 50\text{ Vdc}$ , $V_{GS} = 0\text{ Vdc}$ )	$I_{DSS}$	–	–	0.1 0.5	$\mu\text{Adc}$
Gate-Source Leakage Current ( $V_{GS} = \pm 20\text{ Vdc}$ , $V_{DS} = 0\text{ Vdc}$ )	$I_{GSS}$	–	–	$\pm 0.1$	$\mu\text{Adc}$

**ON CHARACTERISTICS** (Note 1.)

Gate-Source Threshold Voltage ( $V_{DS} = V_{GS}$ , $I_D = 1.0\text{ mAdc}$ )	$V_{GS(th)}$	0.5	–	1.5	Vdc
Static Drain-to-Source On-Resistance ( $V_{GS} = 2.75\text{ Vdc}$ , $I_D < 200\text{ mAdc}$ , $T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$ ) ( $V_{GS} = 5.0\text{ Vdc}$ , $I_D = 200\text{ mAdc}$ )	$r_{DS(on)}$	–	5.6 –	10 3.5	Ohms
Forward Transconductance ( $V_{DS} = 25\text{ Vdc}$ , $I_D = 200\text{ mAdc}$ , $f = 1.0\text{ kHz}$ )	$g_{fs}$	100	–	–	mmhos

**DYNAMIC CHARACTERISTICS**

Input Capacitance	( $V_{DS} = 25\text{ Vdc}$ , $V_{GS} = 0$ , $f = 1\text{ MHz}$ )	$C_{iss}$	–	40	50	pF
Output Capacitance	( $V_{DS} = 25\text{ Vdc}$ , $V_{GS} = 0$ , $f = 1\text{ MHz}$ )	$C_{oss}$	–	12	25	
Transfer Capacitance	( $V_{DG} = 25\text{ Vdc}$ , $V_{GS} = 0$ , $f = 1\text{ MHz}$ )	$C_{rss}$	–	3.5	5.0	

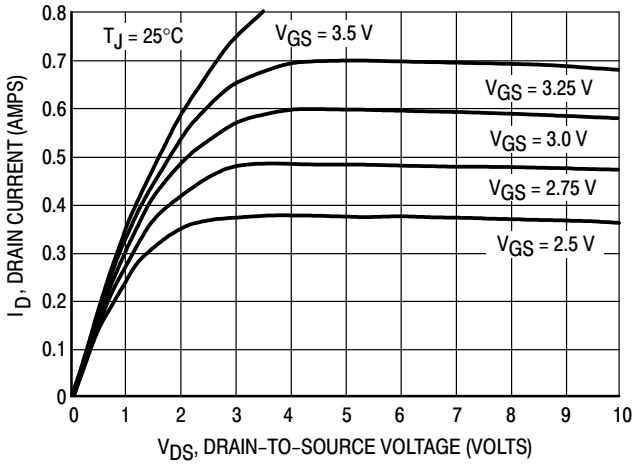
**SWITCHING CHARACTERISTICS** (Note 2.)

Turn-On Delay Time	(V <sub>DD</sub> = 30 Vdc, I <sub>D</sub> = 0.2 Adc,)	$t_{d(on)}$	–	–	20	ns
Turn-Off Delay Time		$t_{d(off)}$	–	–	20	

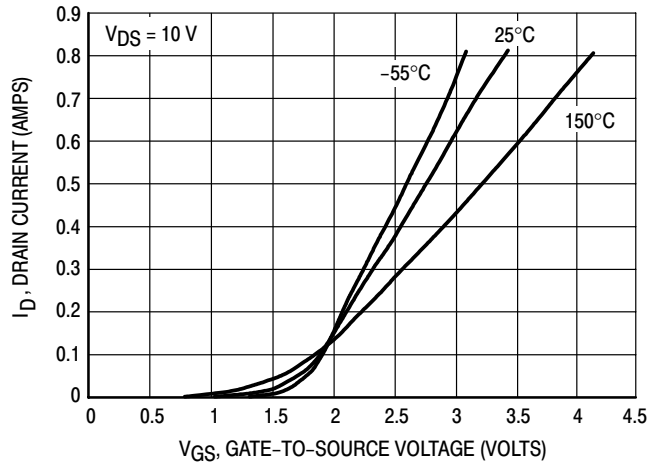
1. Pulse Test: Pulse Width  $\leq 300\ \mu\text{s}$ , Duty Cycle  $\leq 2\%$ .
2. Switching characteristics are independent of operating junction temperature.

**Power MOSFET 200 mAmps, 50 Volts**

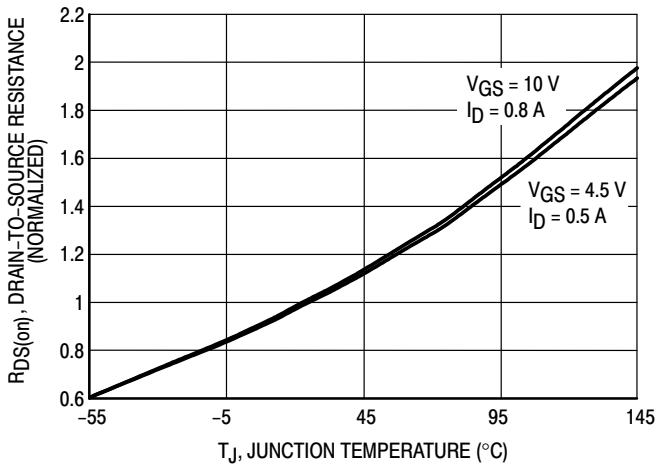
**TYPICAL ELECTRICAL CHARACTERISTICS**



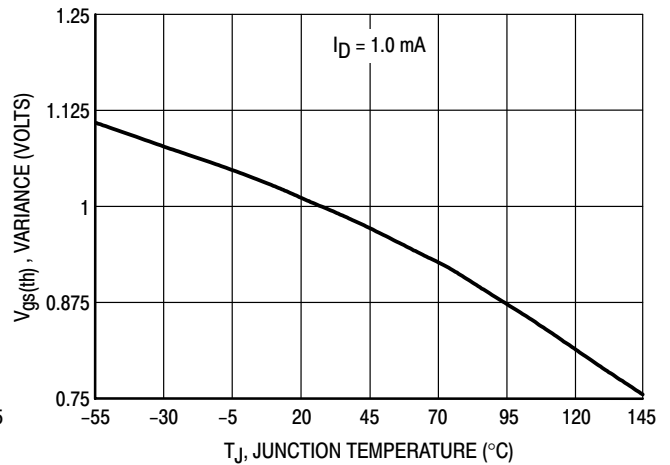
**Figure 1. On-Region Characteristics**



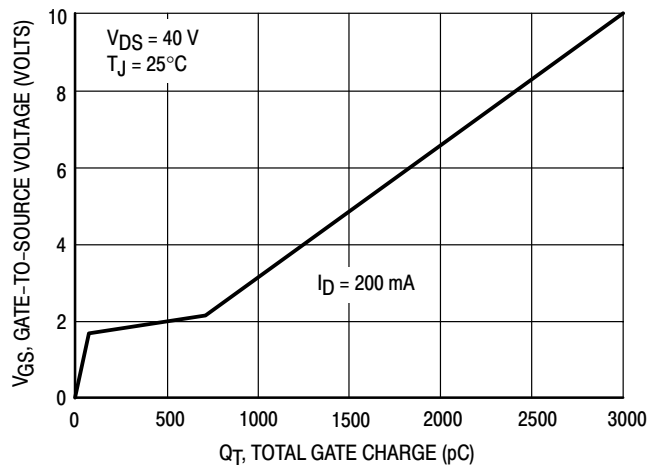
**Figure 2. Transfer Characteristics**



**Figure 3. On-Resistance Variation with Temperature**



**Figure 4. Threshold Voltage Variation with Temperature**



**Figure 5. Gate Charge**

### TYPICAL ELECTRICAL CHARACTERISTICS

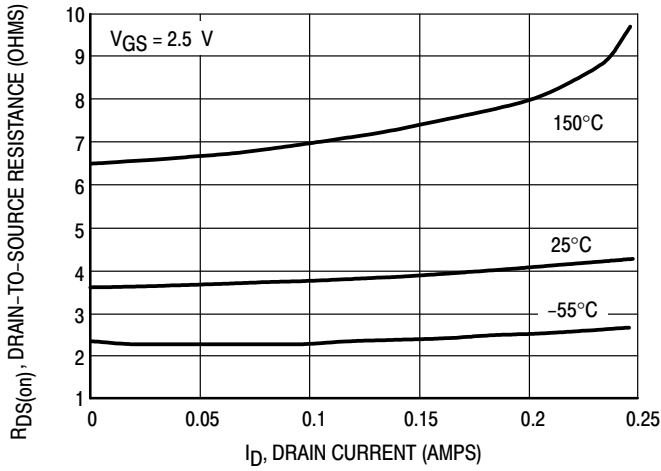


Figure 6. On-Resistance versus Drain Current

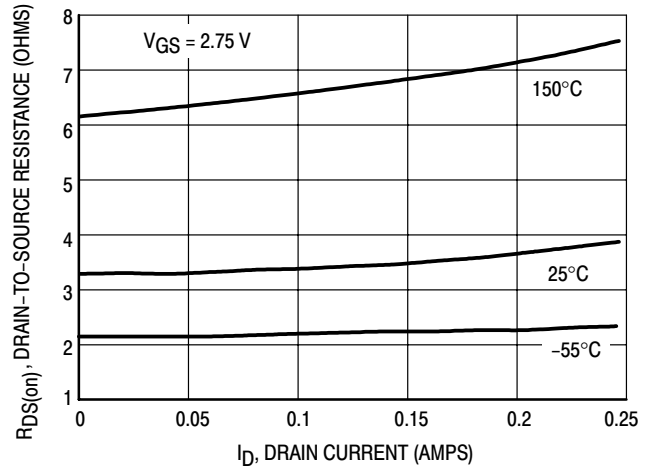


Figure 7. On-Resistance versus Drain Current

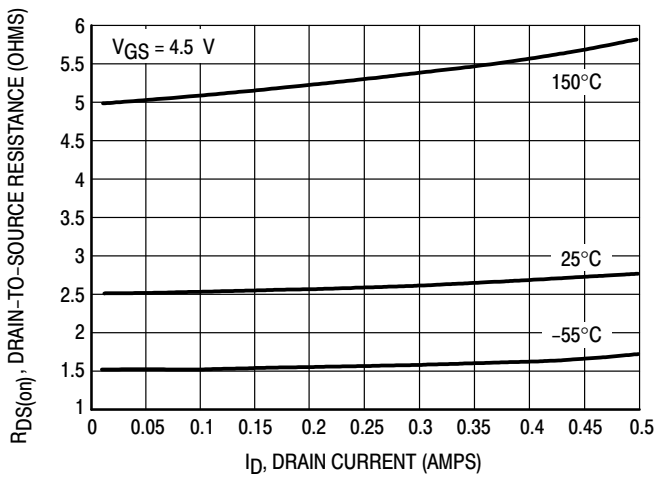


Figure 8. On-Resistance versus Drain Current

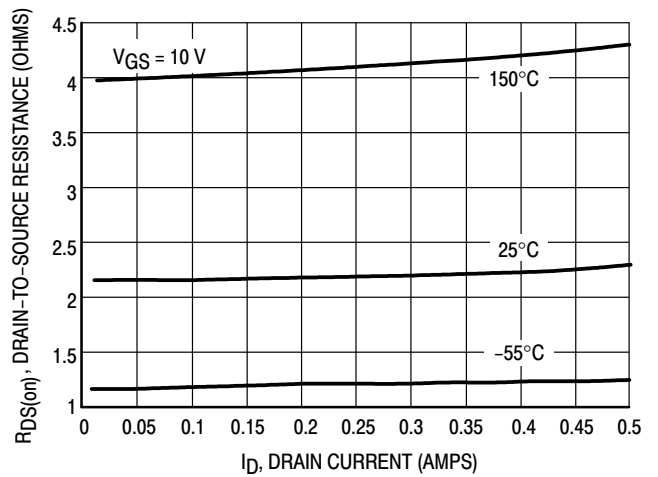


Figure 9. On-Resistance versus Drain Current

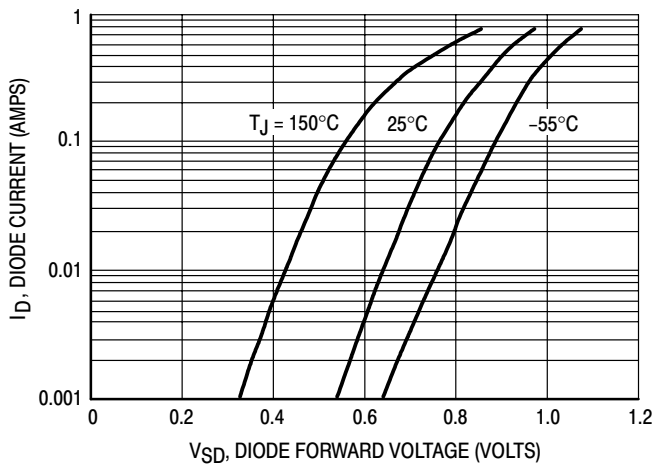


Figure 10. Body Diode Forward Voltage

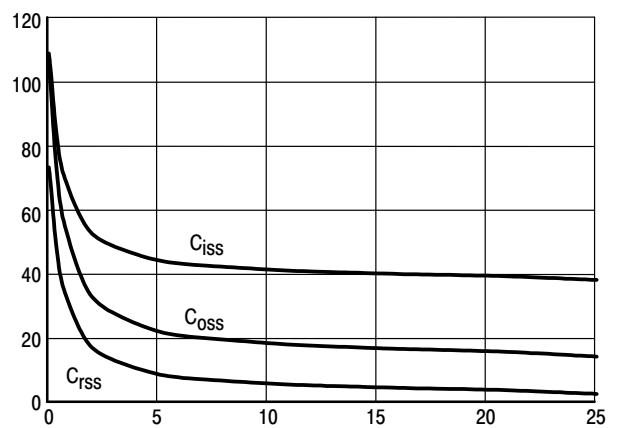
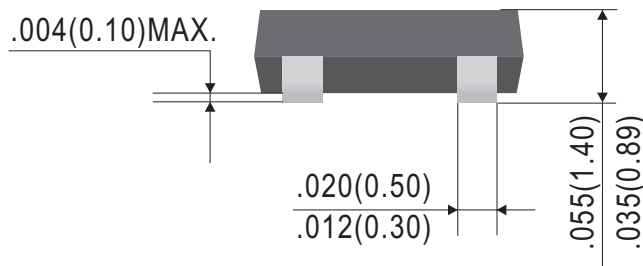
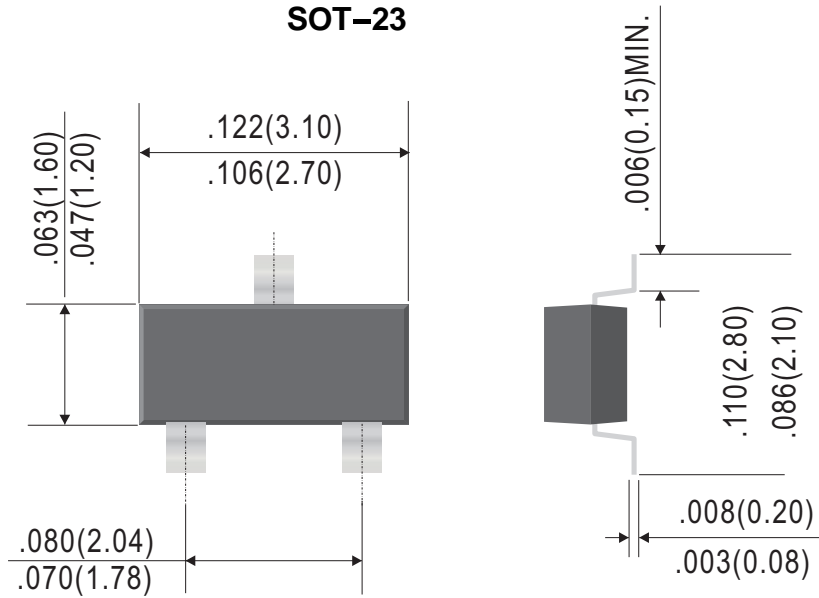


Figure 11. Capacitance



### SOT-23



Dimensions in inches and (millimeters)

